

IN THE CLAIMS:

Replace the indicated claims with:

1. (Amended) A matching circuit for absorbing fluctuation of electrical characteristics of a transistor, comprising a capacitor having a capacitance that increases and decreases opposite to changes in a parasitic capacitance at said transistor.

2. (Amended) The matching circuit according to claim 1, wherein the parasitic capacitance increases and decreases according to a thickness change of an MIM insulation film located around said transistor and said capacitor has an MIM capacitance that increases and decreases opposite to changes in the parasitic capacity.

3. (Amended) The matching circuit according to claim 2, wherein said capacitor is located at an input side of said transistor.

4. (Amended) The matching circuit according to claim 3, comprising a bias circuit connected in parallel with said capacitor.

5. (Amended) The matching circuit according to claim 2, wherein said capacitor is located at an output side of said transistor.

6. (Amended) The matching circuit according to claim 5, comprising a bias circuit connected in parallel with said capacitor.

7. (Amended) The matching circuit according to claim 2, wherein said capacitor is located at an input side of said transistor.

8. (Amended) The matching circuit according to claim 7, comprising a bias circuit connected in parallel with said capacitor.

9. (Amended) The matching circuit according to claim 2, wherein said capacitor is located at an output side of said transistor.

10. (Amended) The matching circuit according to claim 7, comprising a bias circuit connected in parallel with said capacitor.

11. (Amended) A semiconductor device including said matching circuit according to claim 1.

12. (Amended) A semiconductor device including said matching circuit according to claim 2.

IN THE ABSTRACT:

Replace the Abstract with:

Abstract of the Disclosure

A matching circuit that can protect a high frequency circuit from degradation in both output and efficiency, as well as from an increase of noise, and changes of a frequency band even when an MIM insulation film thickness around a subject transistor changes due to an unevenness among fabrication processes. As a result, an electrical property of the transistor never changes among products. An MIM capacitance is connected to an input side of the transistor so as to be combined with an input capacitance of the transistor. Changes of the MIM insulation film thickness can be eliminated automatically. The MIM capacitance changes opposite to the changes of the MIM insulation film thickness. That is, it is possible to realize a matching circuit that can absorb fluctuations of electric characteristics of the subject transistor automatically when the fluctuation of electric characteristics of the transistor are caused by changes of the MIM insulation film thickness around the transistor due to non-uniformities in fabrication processes. In addition, where the matching circuit includes a bias circuit, it is possible to obtain a high frequency circuit that can operate stably in a wide frequency band.